

**PRODUCT RELIABILITY REPORT
FOR**

DS600, Rev A3

Dallas Semiconductor

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Prepared by:

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Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products:

DS600, Rev A3

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at <http://www.maxim-ic.com/TechSupport/dsreliability.html>.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

$$AfT = \exp((Ea/k) * (1/Tu - 1/Ts)) = tu/ts$$

AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10⁻⁵ eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

$$AfV = \exp(B * (Vs - Vu))$$

AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

$$Fr = X / (ts * AfV * AfT * N * 2)$$

X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

$$MTTF = 1/Fr$$

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE:	MTTF (YRS):	64367	FITS:	1.8
	DEVICE HOURS:	547784	FAILS:	0

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60% **Ea: 0.7** **B: 0** **Tu: 25 °C** **Vu: 3.5 Volts**

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. "*" after DATE CODE denotes specific product data.

Device Information:

Process: E35X-3P3M,DPE2,CrSi,DSD,PDES D,PDRES,Cap,ENPN,DPT,HTO,SgHalo
 Passivation: TEOS Ox-Nit Passivation for E35X; Full BEOL at SA; PT only in Dallas
 Die Size: 56 x 56
 Number of Transistors: 3606
 Interconnect: Aluminum / 1% Silicon / 0.5% Copper
 Gate Oxide Thickness: 120 Å

DATA RETENTION

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QTY	FAILS	FA#
STORAGE LIFE	0515	150C	1000 HRS	77	0	
STORAGE LIFE	0617	150C	1000 HRS	77	0	
STORAGE LIFE	0629	150C	1000 HRS	77	0	
			Total:		0	

OPERATING LIFE

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QTY	FAILS	FA#
HIGH TEMP OP LIFE	0451 *	125C, 5.5 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0515	125C, 5.5 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0536	125C, 5.5 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0543	125C, 3.6 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0601	125C, 5.5 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0617	125C, 3.6 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0618	125C, 5.5 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0623	125C, 5.5 V (PSA) & 15.0 V (PSB)	192 HRS	77	0	
HIGH TEMP OP LIFE	0629	125C, 5.5 VOLTS	1000 HRS	77	0	

HIGH TEMP OP LIFE	0640	125C, 5.5 VOLTS	1000 HRS	45	0
Total:					0

W/E ENDURANCE AND DATA RET'N

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QTY	FAILS	FA#
WRITE CYCLE STRESS (KCYS)	0536	50 C, 5.5 VOLTS	50 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0541	50 C, 5.5 VOLTS	50 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	76	0	
WRITE CYCLE STRESS (KCYS)	0541	25 C, 5.5 VOLTS	80 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0541	85 C, 5.5 VOLTS	20 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	76	0	
WRITE CYCLE STRESS (KCYS)	0601	70 C, 5.5 VOLTS	50 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	76	0	
WRITE CYCLE STRESS (KCYS)	0623	50 C, 5.5 V (PSA) & 15.0 V (PSB)	50 KCYS	77	0	
WRITE CYCLE STRESS (KCYS)	0623	85 C, 5.5 V (PSA) & 15.0 V (PSB)	50 KCYS	77	0	
STORAGE LIFE	0626	150C	96 HRS	77	0	
WRITE CYCLE STRESS (KCYS)		85 C, 5.5 VOLTS	50 KCYS	77	0	
WRITE CYCLE STRESS (KCYS)	0640	70 C, 5.5 VOLTS	50 KCYS	77	0	
STORAGE LIFE		150C	96 HRS	77	0	
Total:					0	

FAILURE RATE:	MTTF (YRS):	64367	FITS:	1.8
	DEVICE HOURS:	547784	FAILS:	0